Important Note: 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. 2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

Sixth	Semester	B.E.	Degree	Examina	ation,	Dec.2017	/Jan.2018
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Time: 3 hrs.

Max. Marks:100

Note: Answer any FIVE full questions, selecting atleast TWO questions from each part.

PART – A

- 1 a. Derive transmission line equations by the methods of distributed circuit theory. (09 Marks)
 - b. Define reflection coefficient and derive an expression for reflection coefficient at load in terms of load impedance (05 Marks)
 - c. A generator of I volt, KHz supplies power to 100 km long line terminated Z_0 . The parameters of the line are $R = 10.4 \Omega/\text{km}$, L = 0.00367 H/km, $G = 0.8 \times 10^{-6} \text{V/km}$ and $C = 0.00835 \times 10^{-6} \text{F/km}$. Calculate Z_0 , attenuation constant and phase constant. (06 Marks)
- 2 a. Using the Helmholtz equation, derive the field equations for TE modes in rectangular waveguides. (10 Marks)
 - b. Briefly explain the following microwave devices:
 - i) Hybrid ring
 - ii) Tow hole directional coupler.

(10 Marks)

- 3 a. A typical h-type GaAS Gunndiode has the following parameters: Threshold field = E_{th} = 2800 v/cm, Applied filed = E = 3200 v/cm, Derive length = E = 10 m. Doping concentration = $E_{th} = 10 \text{ m}$. Doping concentration = $E_{th} = 10 \text{ m}$.
 - i) Compute electron drift velocity
 - ii) Calculate the current density
 - iii) Estimate the negative electron mobility.

(04 Marks)

- b. Explain the principle of operation of read diode with suitable diagrams.
- (04 Marks)

c. Explain the parametric amplifier with equivalence circuit.

(10 Marks)

(08 Marks)

- 4 a. For a two-port network, explain the 8-parameters and properties of s-parameters. (10 Marks)
 - b. Two transmission lines of characteristic impedances Z₁ and Z₂ are jointed at plane PP'. Express S parameters in terms of impedances. (10 Marks)

PART - B

- 5 a. With neat sketch, explain the operation of E plane tee and also obtain its S matrix.

 (10 Marks)
 - b. With neat sketch, explain the operation of magic tee and mention its application. (10 Marks)
- 6 a. Explain the construction and field pattern for micro strip line.

b. Show that $Q_d \cong \frac{1}{Tan\theta}$ for a microstrip line. (04 Marks)

c. A Shilded strip line has the following parameters: Dielectric constant of insulator, $t_r = 2.56$; strip width w = 63.5mm; strip thoickness, t = 35mm; shield depth, d = 180mm; compute: i) Characteristics impedance ii) K factor iii) Fringe capacitance. (08 Marks)

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7 a. Define the following terms related to RADAR:

i) Range to a RADAR

ii) Maximum unambiguous range.

(04 Marks)

b. Derive an expression for simple form of the maximum range of the radar. Comment on the radar range equation. (08 Marks)

c. A 10 GHz radar has the following characteristics: Peak transmitted power = P_t = 250 kW; power gain of antenna = G = 2500; Minimum detectable peak signal power by the receiver = S_{min} = 10^{-14} W. Radar cross section of the target = $6 \ 2m^2$; cross – sectional area of the radar antenna – $10m^2$. Find the maximum range (R_{max}) possible. (03 Marks)

d. State and briefly explain applications of RADAR.

(05 Marks)

8 a. Explain the principle and working of MTI radar, with the help of block diagram. (10 Marks)

b. Write brief notes on:

i) Blind speed

ii) Delay line canceller.

(10 Marks)